

METHOD OF FORMING BOTTOM OXIDE LAYER IN TRENCH STRUCTURE

ABSTRACT OF THE DISCLOSURE

Embodiments of the invention are directed to a method of forming a bottom oxide in a trench structure. In one embodiment, the method includes steps of providing a semiconductor substrate and forming a trench structure in the semiconductor substrate; performing an PECVD process with TEOS as a source to deposit an oxide layer on the bottom and sidewall of the trench structure and the semiconductor substrate; and removing the oxide layer on the sidewall of the trench structure substantially completely and the oxide layer on the bottom of the trench structure partially to define the remained oxide layer as the bottom oxide layer.

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